## Silicon N-Channel MOS FET

# **HITACHI**

ADE-208-1292 (Z) 1st. Edition Mar. 2001

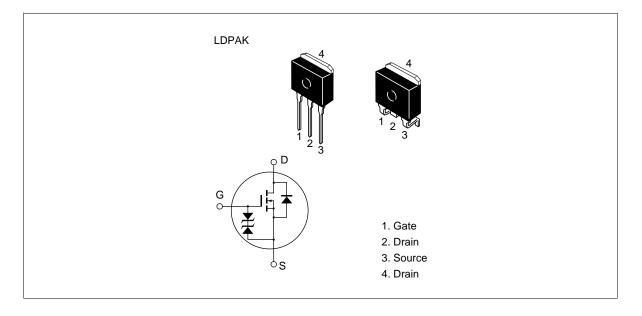
### **Application**

High speed power switching

#### **Features**

- Low on-resistance
- High speed switching
- Low drive current
- · No secondary breakdown
- Suitable for switching regulator and DC-DC converter

#### **Outline**





### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1540	$V_{ t DSS}$	450	V
	2SK1541		500	
Gate to source voltage		$V_{GSS}$	±30	V
Drain current		I <sub>D</sub>	7	Α
Drain peak current		l <sub>D(pulse)</sub> *1	28	Α
Body to drain diode reverse	e drain current	I <sub>DR</sub>	7	Α
Channel dissipation		Pch*2	60	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

Note

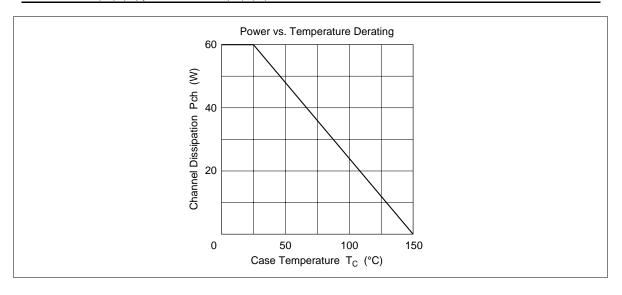
- 1. PW 10 μs, duty cycle 1%
- 2. Value at  $T_c = 25$ °C

#### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

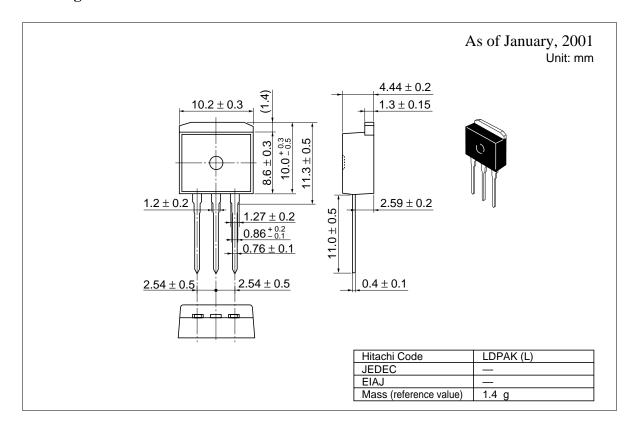
Item		Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source 2	SK1540	$V_{(BR)DSS}$	450	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
breakdown voltage 2	SK1541		500	_			
Gate to source breakdown voltage		$V_{(BR)GSS}$	±30	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current		I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage 2	SK1540	I <sub>DSS</sub>	_	_	250	μΑ	$V_{DS} = 360 \text{ V}, V_{GS} = 0$
drain current 2	SK1541						$V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source cutoff vo	oltage	$V_{GS(off)}$	2.0	_	3.0	V	$I_{D} = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static Drain to source 2	SK1540		_	0.6	0.8		$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
on state resistance 2	SK1541		_	0.7	0.9	_	
Forward transfer admittance		yfs	4.0	6.5	_	S	$I_D = 4 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance		Ciss	_	1050	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance		Coss	_	280	_	pF	f = 1 MHz
Reverse transfer capac	itance	Crss	_	40	_	pF	_
Turn-on delay time		t <sub>d(on)</sub>	_	15	_	ns	$I_D = 4 A, V_{GS} = 10 V,$
Rise time		t <sub>r</sub>	_	55	_	ns	$R_{L} = 7.5$
Turn-off delay time		$t_{d(off)}$	_	95	_	ns	_
Fall time		t <sub>f</sub>	_	40	_	ns	_
Body to drain diode forv	vard	$V_{DF}$	_	0.95	_	V	$I_F = 7 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	erse	t <sub>rr</sub>	_	320	_	ns	$I_F = 7 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A/}\mu\text{s}$

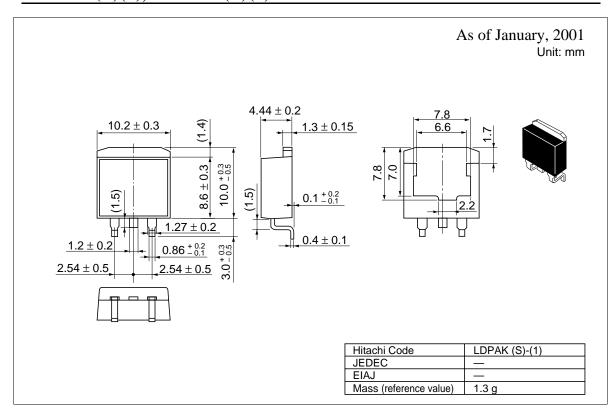
Note 1. Pulse test

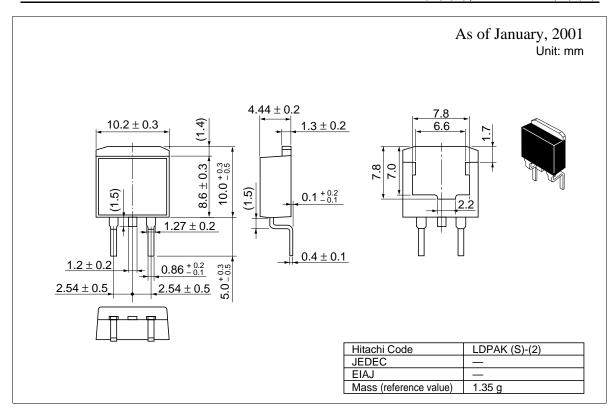
See characteristic curves of 2SK1157, 2SK1158.



#### **Package Dimensions**







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